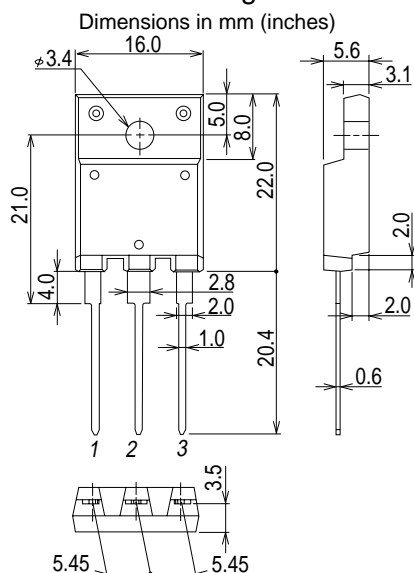


TO247-AI Package Outline.


Pin 1 = Gate Pin 2 = Drain Pin 3 = Source

N-CHANNEL ENHANCEMENT MODE HIGH VOLTAGE ISOLATED POWER MOSFETS

V_{DSS} **1500V**

$I_{D(cont)}$ **2A**

$R_{DS(on)}$ **8.00Ω**

ABSOLUTE MAXIMUM RATINGS ($T_{AMB} = 25^{\circ}\text{C}$ unless otherwise stated)

V_{DSS}	Drain – Source Voltage	1500	V
I_D	Continuous Drain Current	2	A
I_{DM}	Pulsed Drain Current	4	A
V_{GS}	Gate – Source Voltage	±20	V
P_D	Total Power Dissipation	50	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	–55 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_{AMB} = 25^{\circ}\text{C}$ unless otherwise stated)

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0V, I_D = 1mA$	1500			V
$R_{DS(ON)}$	Drain – Source On State Resistance	$V_{GS} = 10V, I_D = 1A$		8.0	11.0	Ω
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1200V, V_{GS} = 0V$			100	μA
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 16V, V_{DS} = 0V$			10	μA
$V_{GS(off)}$	Cutoff Voltage	$V_{DS} = 10V, I_D = 1.0mA$	2.5		3.5	V
C_{iss}	Input Capacitance	$V_{DS} = 20V$ $f = 1MHz$		400		pF
C_{oss}	Output Capacitance			85		
C_{rss}	Reverse Transfer Capacitance			45		
t_{on}	Turn-on Time	$V_{GS} = 10V$		30		ns
t_{off}	Turn-off Time	$I_D = 1A$		200		
V_{SD}	Diode Forward Voltage	$V_{GS} = 0, I_S = 2A$		0.9	1.2	V
$ Y_{FS} $	Forward Transfer Admittance	$V_{DS} = 20V, I_D = 1A$	0.7	1.5		S

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